

N-channel 650 V, 0.073 Ω typ., 30 A MDmesh™ V Power MOSFETs in D²PAK, TO-220 and TO-247 packages

Datasheet - production data

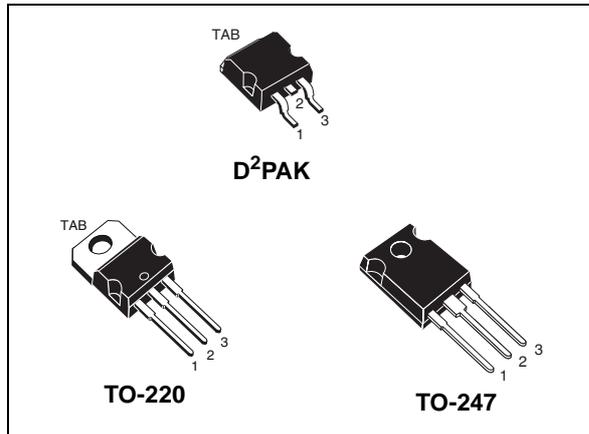
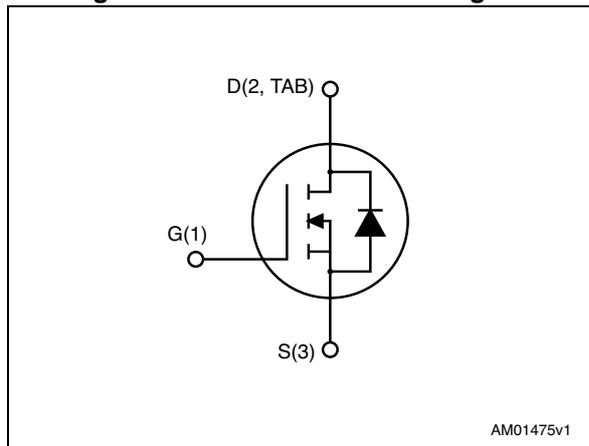


Figure 1. Internal schematic diagram



Features

Order codes	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	I_D
STB38N65M5	710 V	0.095 Ω	30 A
STP38N65M5			
STW38N65M5			

- Higher V_{DSS} rating and high dv/dt capability
- Excellent switching performance
- 100% avalanche tested

Applications

- Switching applications

Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB38N65M5	38N65M5	D ² PAK	Tape and reel
STP38N65M5		TO-220	Tube
STW38N65M5		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
4.1	D2PAK, STB38N65M5	11
4.2	TO-220, STP38N65M5	14
4.3	TO-247, STW38N65M5	16
5	Packaging mechanical data	18
6	Revision history	20

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	30	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	19	A
$I_{DM}^{(1)}$	Drain current (pulsed)	120	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	190	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 30\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{Peak} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		D ² PAK	TO-220	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.66			$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	30			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max		62.5	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1inch² FR-4 board, 2 oz Cu.

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	8	A
E_{AS}	Single pulse avalanche energy (starting $t_j = 25\text{ }^\circ\text{C}$, $I_d = I_{AR}$; $V_{dd} = 50\text{ V}$)	660	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$			1	μA
		$V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$		0.073	0.095	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	3000	-	pF
C_{oss}	Output capacitance		-	74	-	pF
C_{riss}	Reverse transfer capacitance		-	5.8	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0$	-	244	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	70	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	2.4	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 15\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 18)	-	71	-	nC
Q_{gs}	Gate-source charge		-	18	-	nC
Q_{gd}	Gate-drain charge		-	30	-	nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 20\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19 and Figure 22)	-	66	-	ns
$t_{r(v)}$	Voltage rise time		-	9	-	ns
$t_{f(i)}$	Current fall time		-	9	-	ns
$t_{c(off)}$	Crossing time		-	13	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		30	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		120	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 30\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 30\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 22)	-	382		ns
Q_{rr}	Reverse recovery charge		-	6.6		μC
I_{RRM}	Reverse recovery current		-	35		A
t_{rr}	Reverse recovery time	$I_{SD} = 30\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 22)	-	522		ns
Q_{rr}	Reverse recovery charge		-	10.3		μC
I_{RRM}	Reverse recovery current		-	40		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK and TO-220

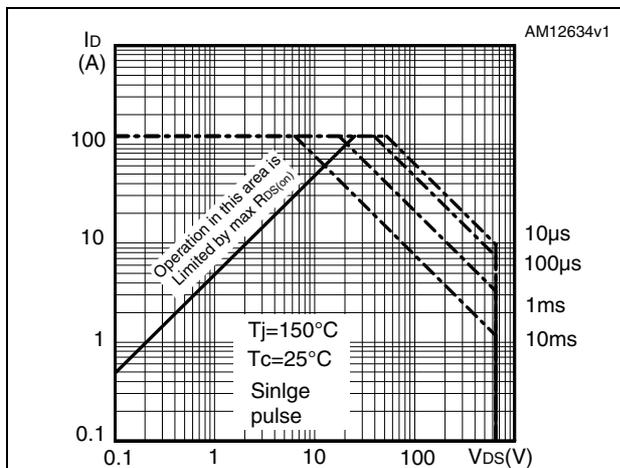


Figure 3. Thermal impedance for D²PAK and TO-220

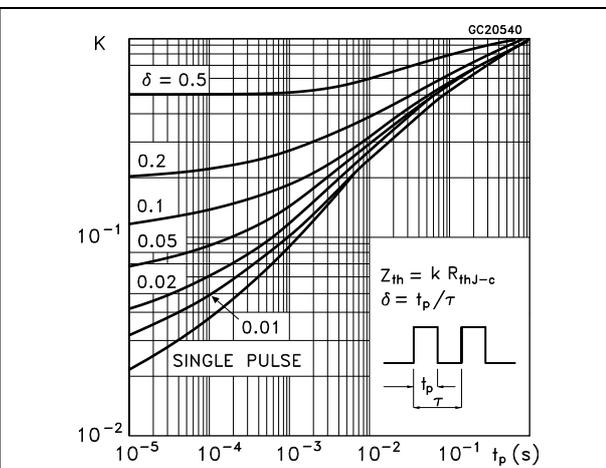


Figure 4. Safe operating area for TO-247

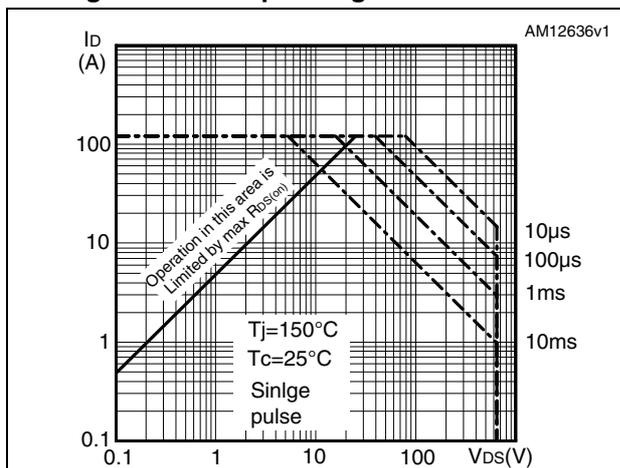


Figure 5. Thermal impedance for TO-247

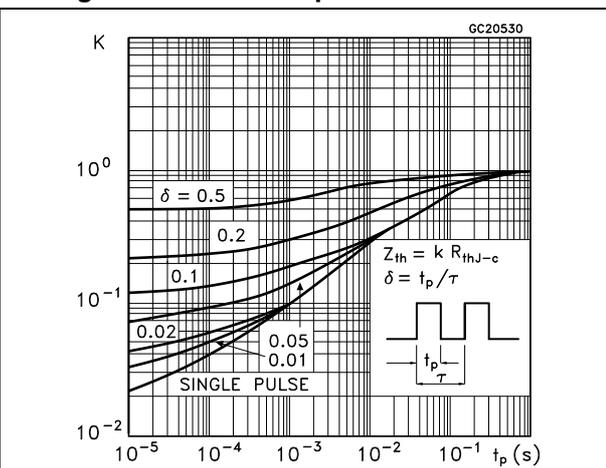


Figure 6. Output characteristics

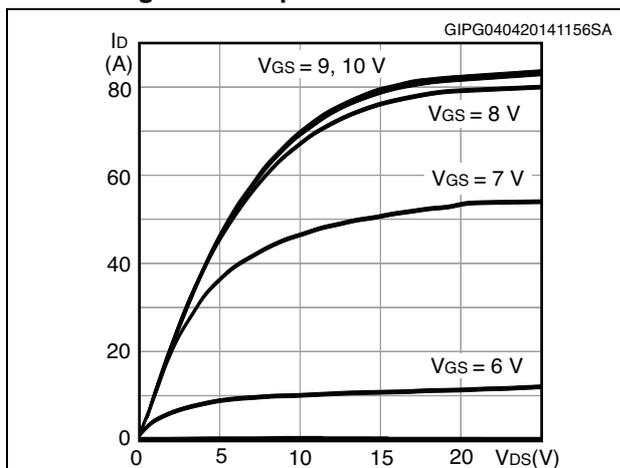


Figure 7. Transfer characteristics

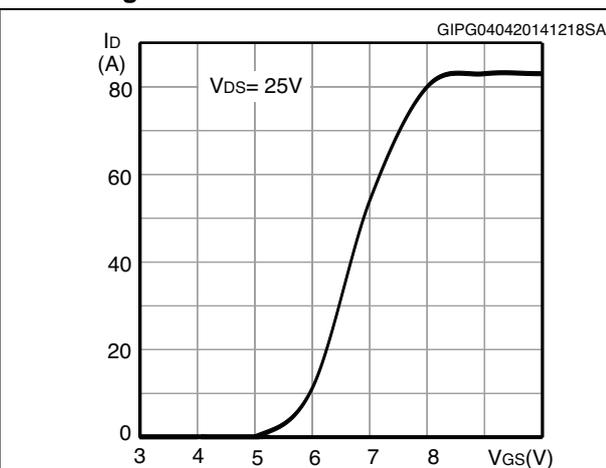


Figure 8. Gate charge vs gate-source voltage

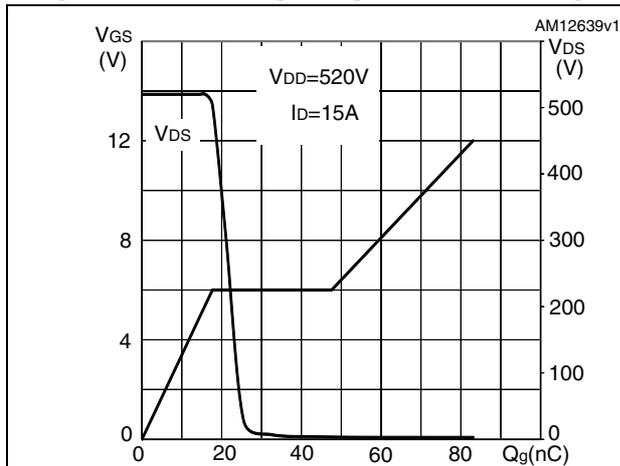


Figure 9. Static drain-source on-resistance

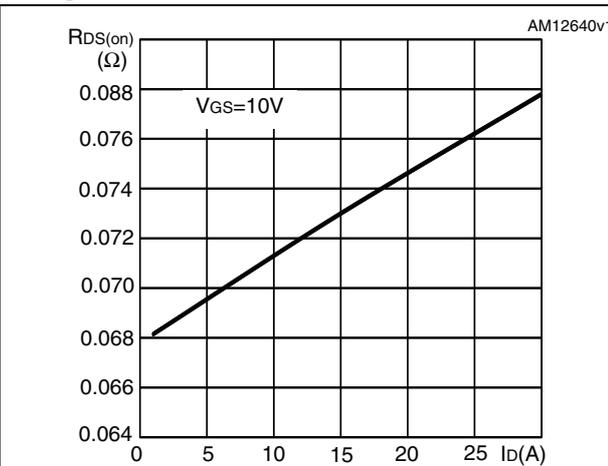


Figure 10. Capacitance variations

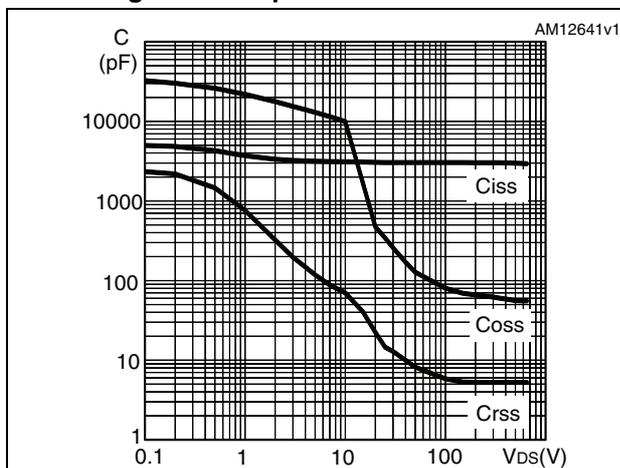


Figure 11. Output capacitance stored energy

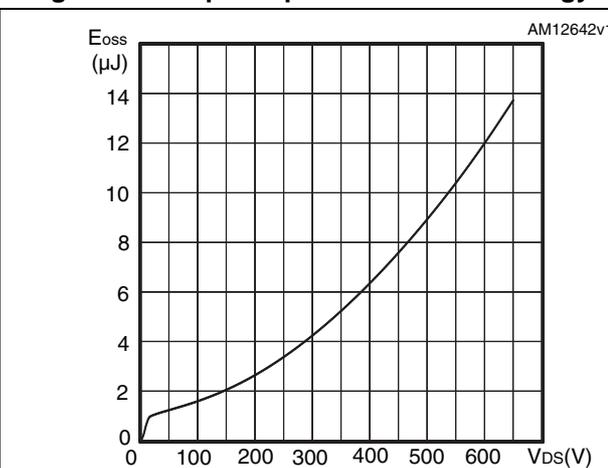


Figure 12. Normalized gate threshold voltage vs temperature

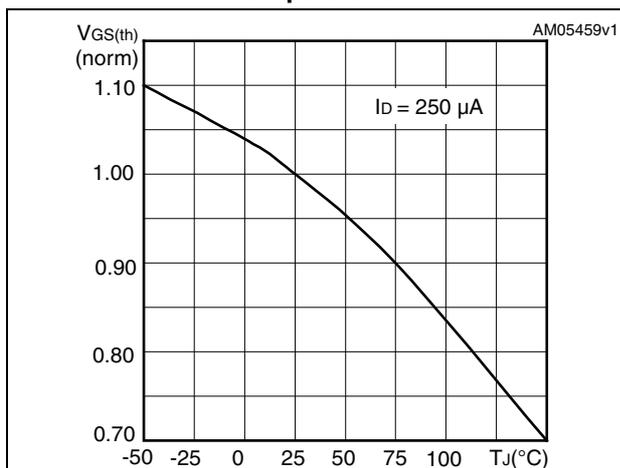


Figure 13. Normalized on-resistance vs temperature

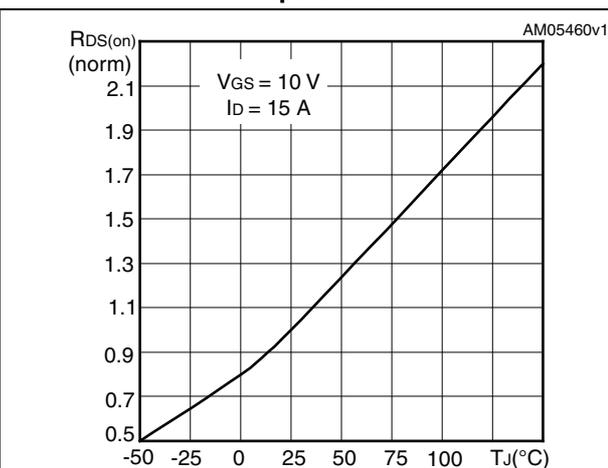


Figure 14. Source-drain diode forward characteristics

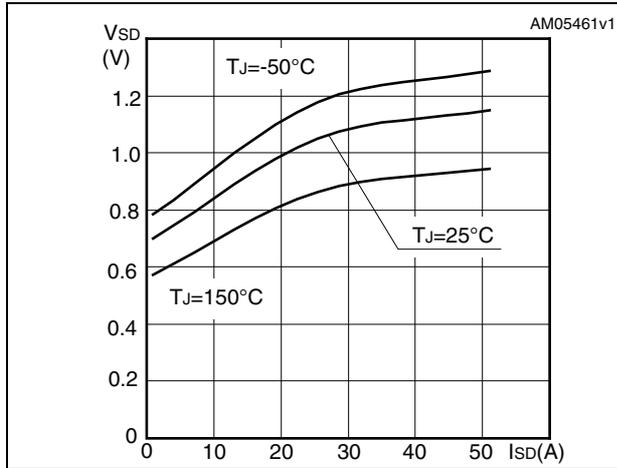


Figure 15. Normalized $V_{(BR)DSS}$ vs temperature

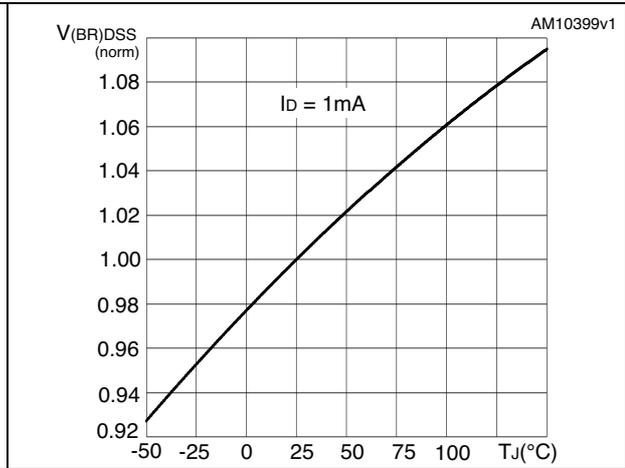
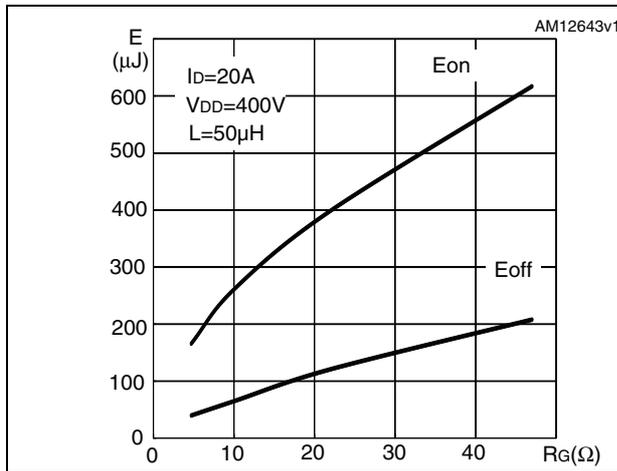


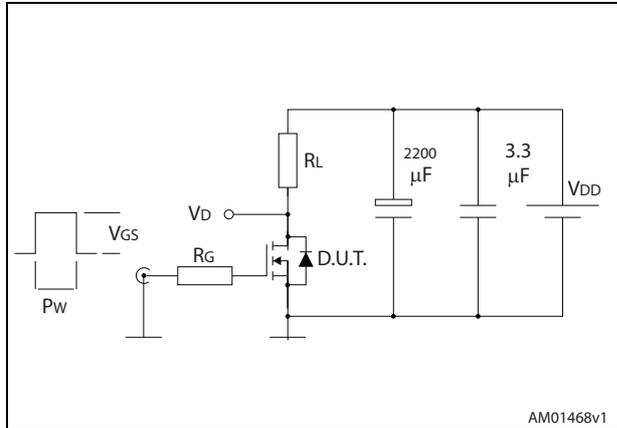
Figure 16. Switching losses vs gate resistance (1)



1. E_{on} including reverse recovery of a SiC diode.

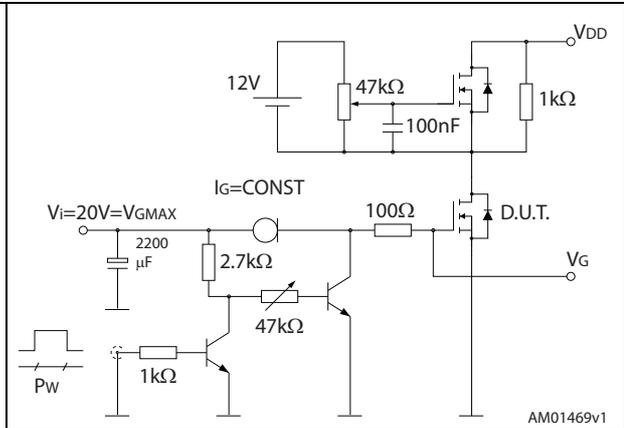
3 Test circuits

Figure 17. Switching times test circuit for resistive load



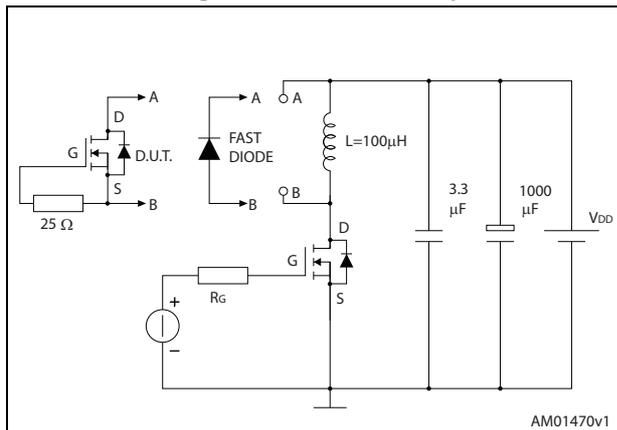
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Figure 18. Gate charge test circuit



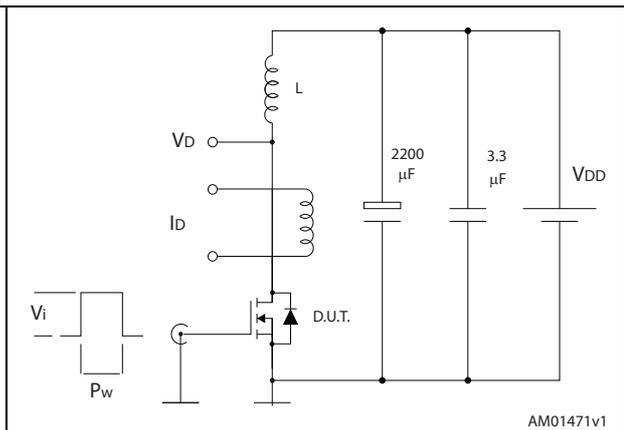
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Figure 19. Test circuit for inductive load switching and diode recovery times



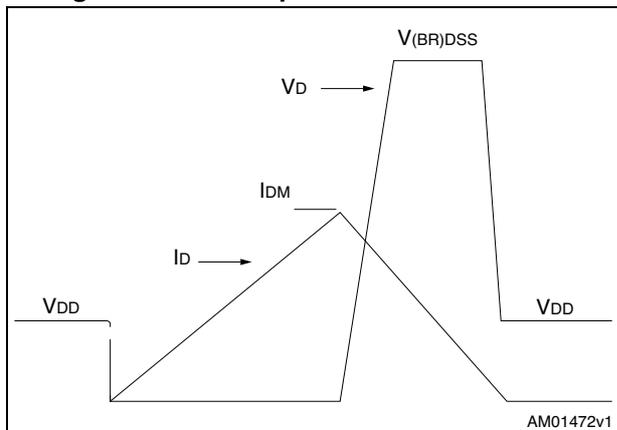
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Figure 20. Unclamped inductive load test circuit



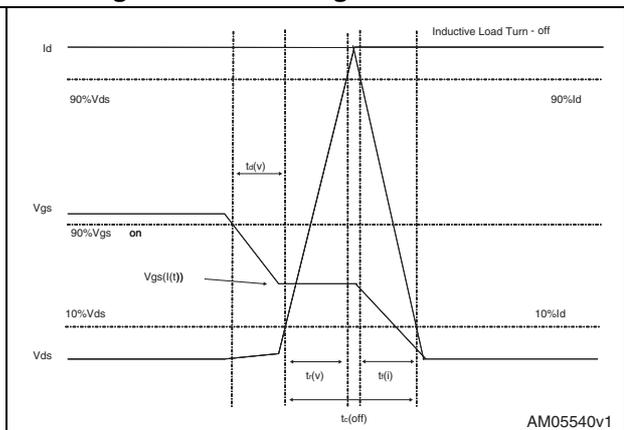
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Figure 21. Unclamped inductive waveform



AM01472v1

Figure 22. Switching time waveform



AM05540v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 D²PAK, STB38N65M5

Figure 23. D²PAK (TO-263) drawing

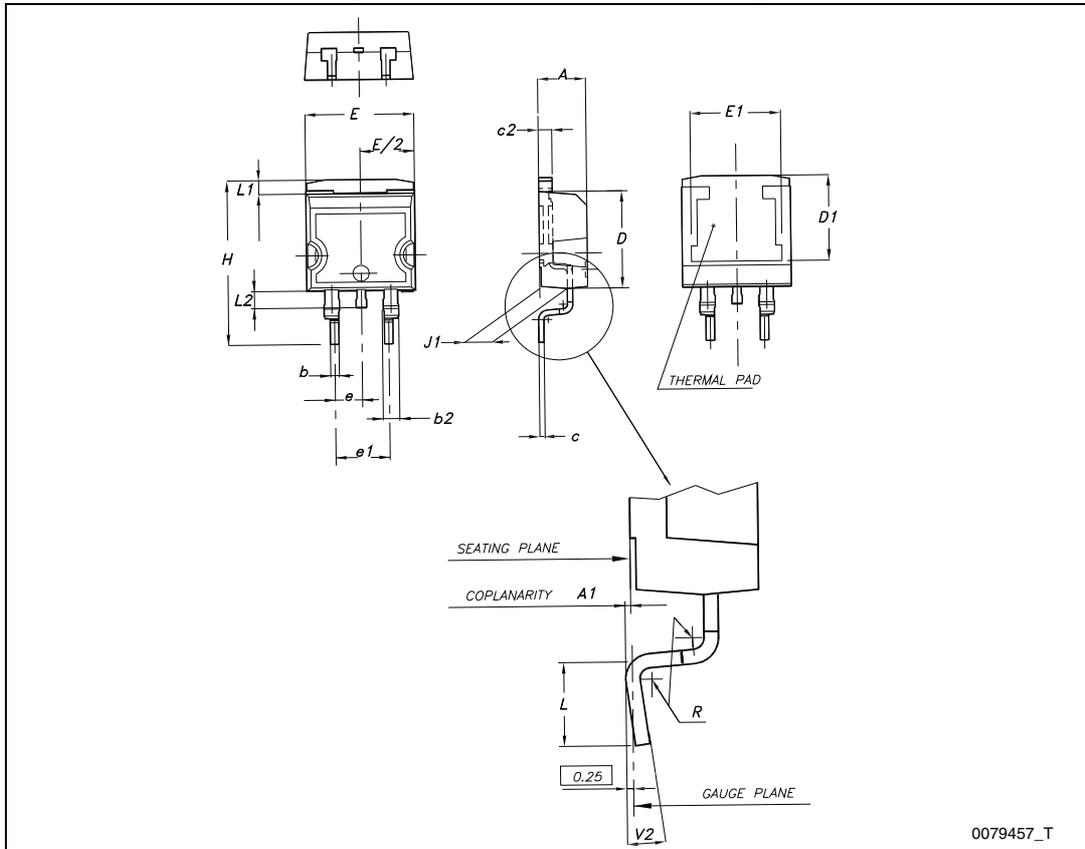
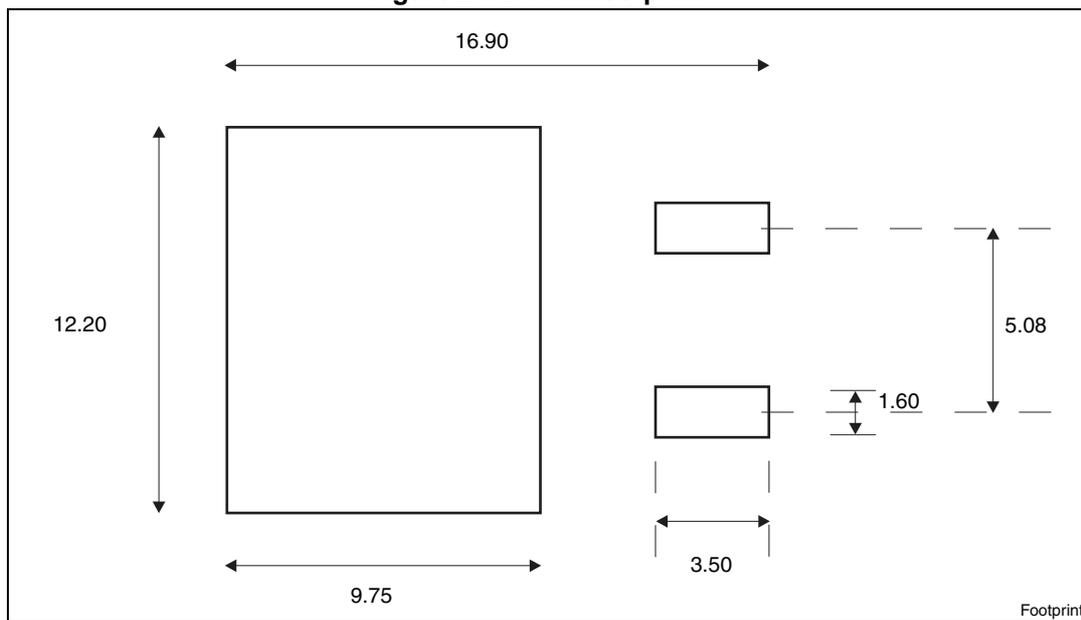


Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK footprint^(a)



a. All dimension are in millimeters

4.2 TO-220, STP38N65M5

Figure 25. TO-220 type A drawing

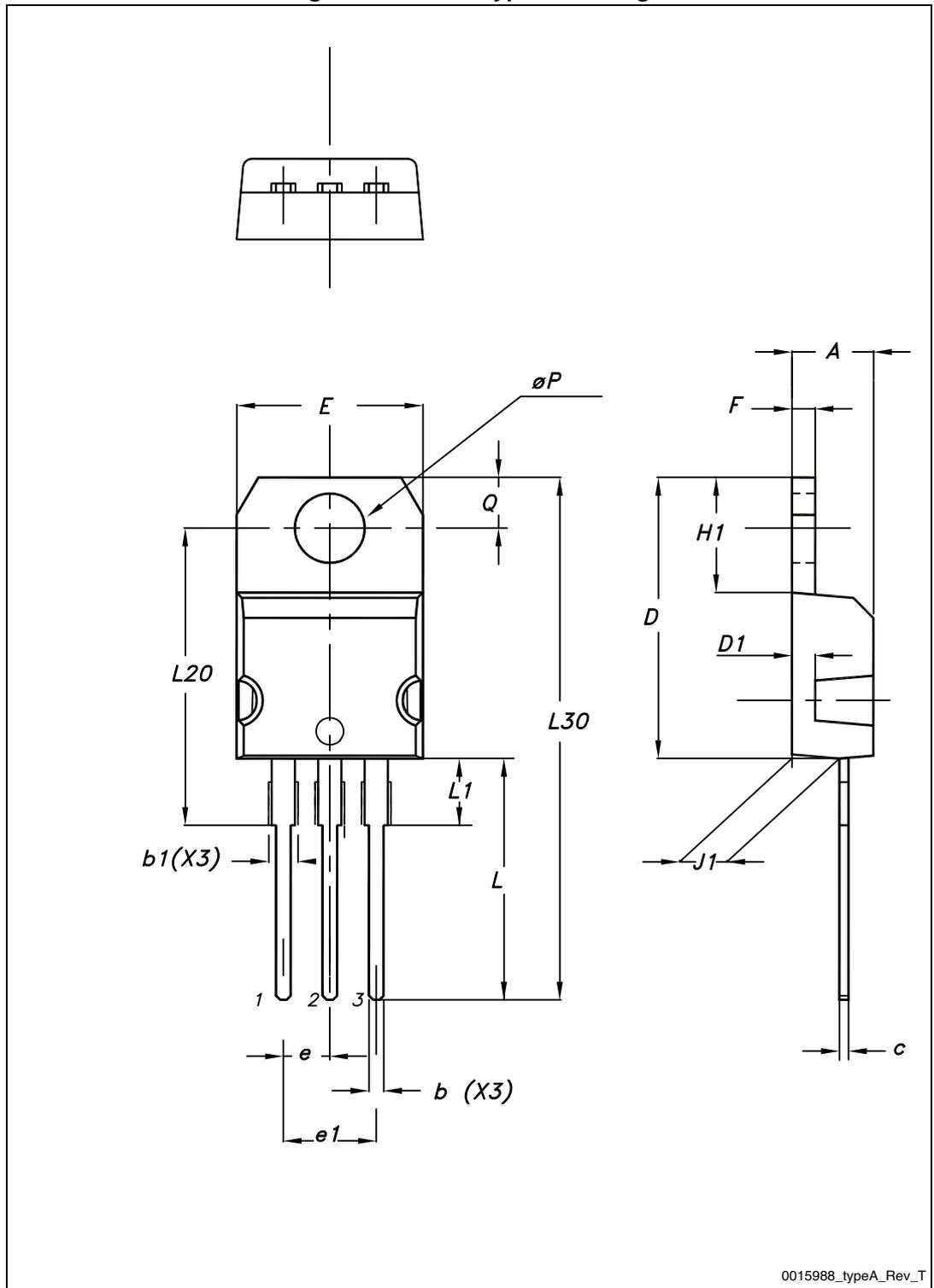


Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

4.3 TO-247, STW38N65M5

Figure 26. TO-247 drawing

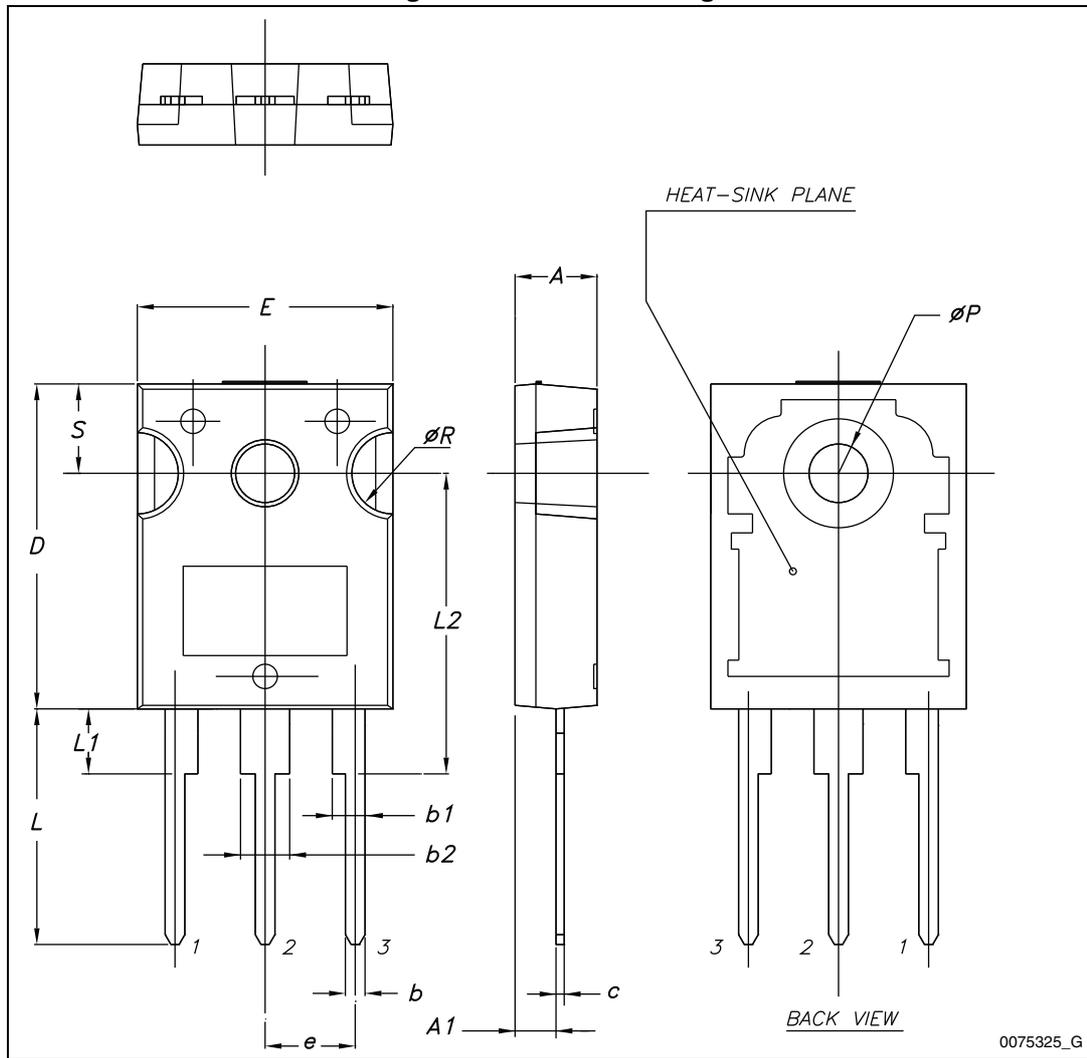


Table 11. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Packaging mechanical data

Figure 27. Tape

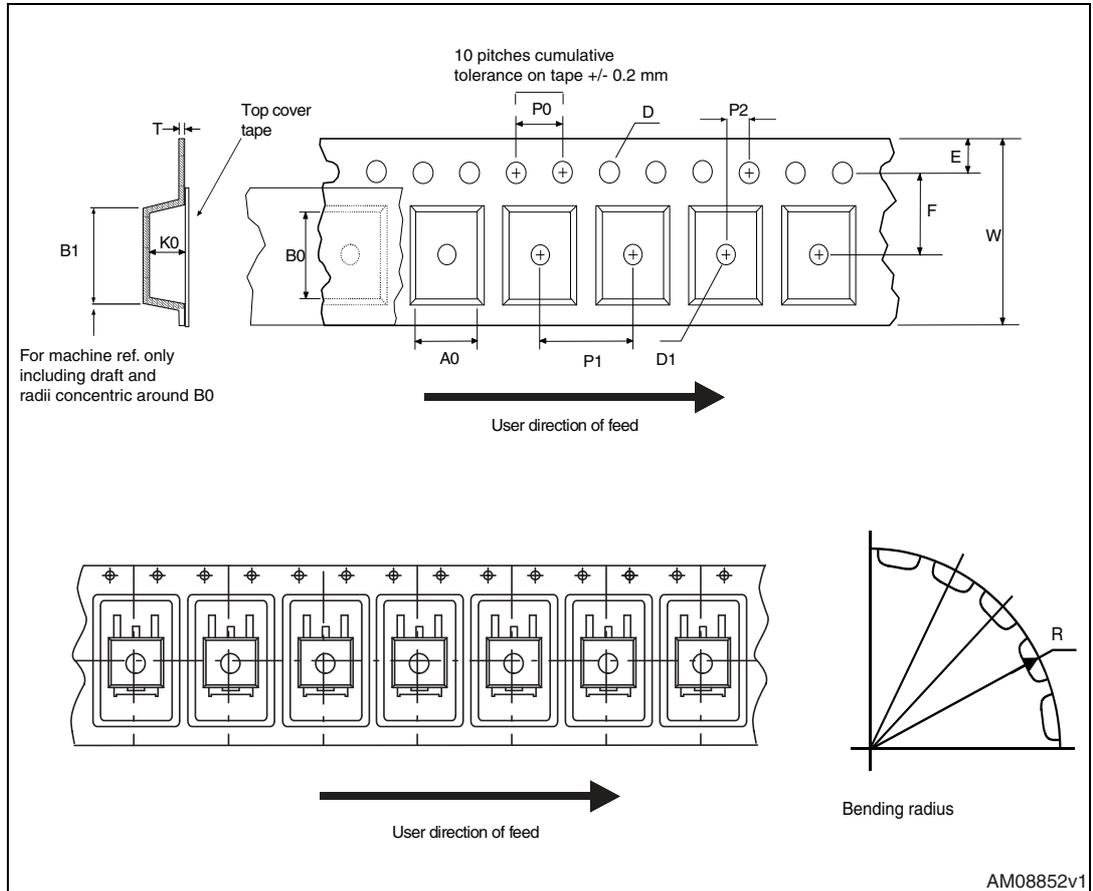


Figure 28. Reel

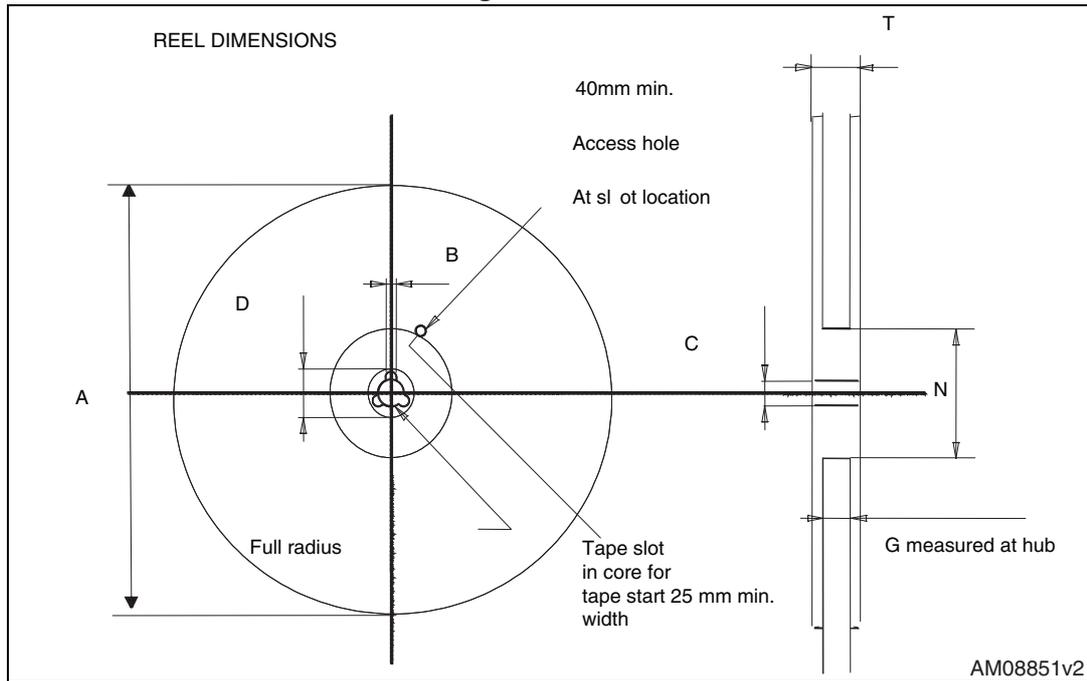


Table 12. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

6 Revision history

Table 13. Document revision history

Date	Revision	Changes
22-Feb-2012	1	First release.
21-Jun-2012	2	Document status changed from preliminary data to production data. Added Section 2.1: Electrical characteristics (curves) .
05-Mar-2013	3	Added dv/dt value on Table 2: Absolute maximum ratings .
09-Apr-2014	4	<ul style="list-style-type: none">– The part number STF38N65M5 has been moved to a separate datasheet– Minor text changes

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